

Dual ultrafast power diode 22 February 2018

Product data sheet

1. General description

Dual ultrafast power diodes in a TO3PF plastic package.

2. Features and benefits

- · Very low on-state loss
- · Reduces switching losses in associated MOSFET or IGBT
- Low leakage current
- Isolated plastic package

3. Applications

- Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _R	reverse voltage	DC	-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5; T _h ≤ 101 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	-	15	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 µs; T _h ≤ 101 °C; Square-ware pulse	-	-	30	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	-	150	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	-	165	A
Static chara	acteristics			·		
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.4	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	-	V
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	I_F = 1 A; V _R = 30 V; dI _F /dt = 100 A/µs; T _j = 25 °C; <u>Fig. 7</u>	-	38	-	ns
		I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_j = 25 °C; <u>Fig. 7</u>	-	67	-	ns
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _j = 125 °C; <u>Fig. 7</u>	-	106	-	ns

5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode		
3	A2	anode 2		K sym125
mb	mb	mounting base	TO3PF	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYV415J-600P	TO3PF	Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'	TO3PF			

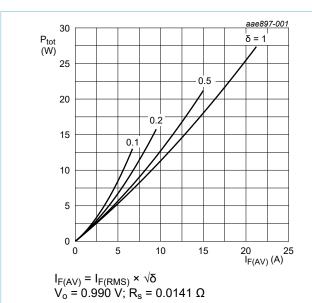
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7. Limiting values

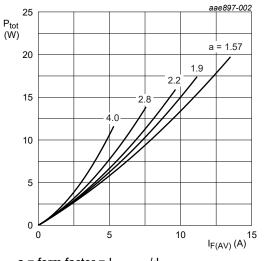
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h ≤ 101 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	A
I _{O(AV)}	average output current	δ = 0.5 ; T _h ≤ 90 °C; square-wave pulse; both diodes conducting	-	30	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ; t_p$ = 25 µs; T_h $\leq \ $ 101 °C; Squareware pulse	-	30	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	150	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	-	165	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C







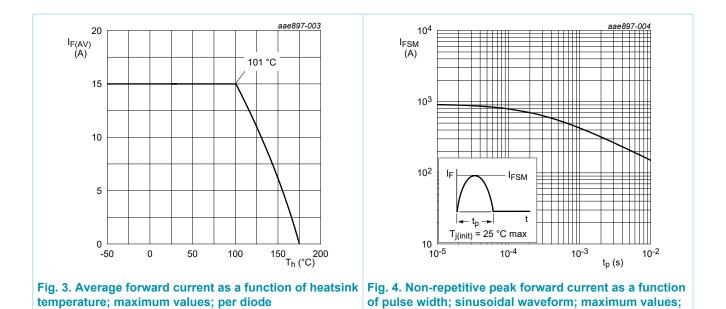
a = form factor = I $_{F(RMS)}$ / I $_{F(AV)}$ V $_o$ = 0.990 V; R $_s$ = 0.0141 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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per diode

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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; per diode; Fig. 5	-	2.9	3.5	K/W
		with heatsink compound; both diodes conducting	-	1.6	2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W

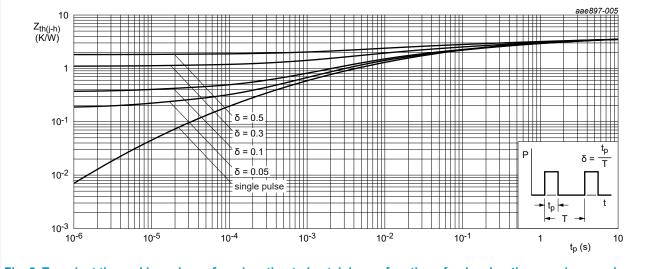
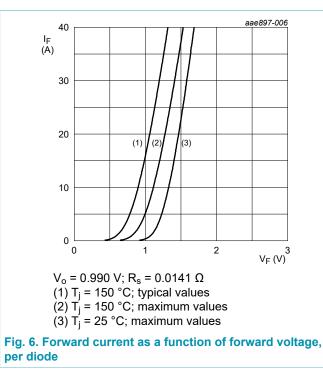


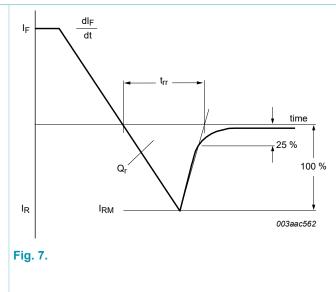
Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse duration; maximum values; per diode

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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara					interv	
	acteristics					
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.17	1.4	V
		I _F = 15 A; T _j = 150 °C; <u>Fig. 6</u>	-	1	-	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	500	μA
Dynamic ch	naracteristics	· · · · · ·				,
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	38	-	ns
		I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_j = 25 °C; Fig. 7	-	67	-	ns
		I_F = 15 A; V_R = 200 V; dI_F/dt = 200 A/ µs; T_j = 125 °C; <u>Fig. 7</u>	-	106	-	ns
I _{RM}	peak reverse recovery current	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 25 \text{ °C}; Fig. 7$	-	9.8	-	A
		$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	16	-	A
Q _r	recovered charge	$I_F = 15 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; T _j = 25 °C; <u>Fig. 7</u>	-	329	-	nC
		I _F = 15 A; V _R = 200 V; dI _F /dt = 200 A/ μs; T _i = 125 °C; <u>Fig. 7</u>	-	876	-	nC

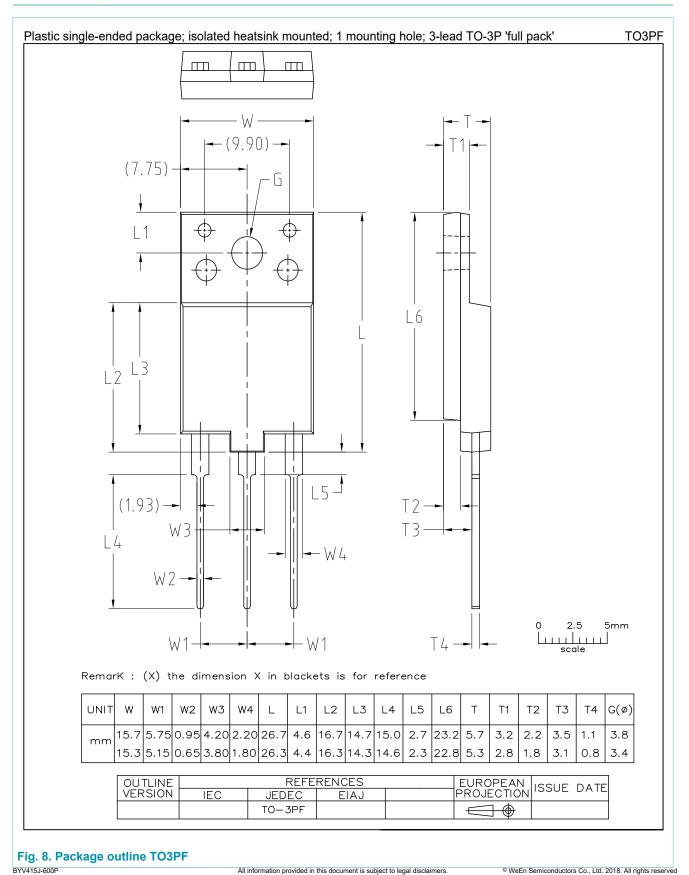




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10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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